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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

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OTHER R	EFER	ENCES (inclu	iding Author	, Title, Date, Pertin	ent Pages, Etc	.)				
UG	AN	ARMA: 1987.	S, B., et al., "CI The Electrocher	nemical Vapor Depositio nical Society, Inc., Proce	n Of Si₃N₄ and AIN eedings Vol 87-8, p	on Carbon F p. 1060-69 (1	ibers", <u>Chemi</u> 987)	cal Vapor De	eposition	

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\top	AC	5,605,858	02/97	NISHIOKA ET AL.				
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Y	AS	Number JP401230779A	09/14/89	Hayashi et al.			Yes	No
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